

It is recommended that the electrical connections to the bonding pads be made using 0.7-1.0 mil diameter gold wire. The microwave/millimeter-wave connections should be kept as short as possible to minimize inductance. For assemblies requiring long bond wires, multiple wires can be attached to the RF bonding pads.

Thermosonic wedge is the preferred method for wire bonding to the gold bond pads. A guided-wedge at an ultrasonic power level of 64 dB can be used for the 0.7 mil wire. The recommended wire bond stage temperature is $150 \pm 2^{\circ}\text{C}$.

For more detailed information see HP application note #999, "GaAs MMIC Assembly and Handling Guidelines."

*GaAs MMICs are ESD sensitive.
Proper precautions should be used*

26

22

11

RF Output Power (dBm)

